

IN THE CLAIMS

Per the revised amendment practice, a complete listing of all claims in the application follows.

Claims 1-58 (Cancelled).

59. (Original) A method of forming oxide over a transistor gate and over a substrate extending laterally from under said gate, said method comprising:

- forming an undoped first oxide over said gate and said substrate;
- forming an undoped second oxide over said first oxide;
- doping said second oxide after forming said second oxide;
- depositing insulation over said second oxide after doping said second oxide;
- initiating a removal of a portion of said insulation; and
- stopping said removal with said second oxide.

60. (Original) The method in claim 59, wherein said step of forming an undoped first oxide comprises forming a TEOS-based oxide.

61. (Original) The method in claim 59, wherein said step of forming an undoped first oxide comprises forming a continuous silicon dioxide layer.

62. (Original) The method in claim 59, wherein said step of forming an undoped first oxide comprises forming a first oxide that is thicker over said gate than lateral to said gate, and wherein said first oxide is thicker over said substrate than lateral to said gate.

63. (Original) The method in claim 62, wherein said step of forming an undoped first oxide comprises forming a non-porous first oxide.

64. (Original) The method in claim 62, wherein said step of forming an undoped second oxide comprises forming a second oxide that is thicker over said gate than lateral to said gate, and wherein said second oxide is thicker over said substrate than lateral to said gate.

65. (Original) The method of claim 64, wherein said step of forming an undoped second oxide comprises:

depositing 500 to 1000 Angstroms of said second oxide over said gate;
depositing 500 to 1000 Angstroms of said second oxide over said substrate; and
depositing 0 to 50 Angstroms of said second oxide lateral to said gate.

Claims 66-68 (Cancelled).

69. (Currently amended) ~~The method in claim 68~~ A method of depositing an interlayer dielectric, comprising:

providing a first level of a semiconductor device, said first level defining a topography and comprising insulation;
depositing BSG onto discrete portions of said topography, said BSG having a dielectric constant of at most 3, wherein said step of depositing BSG comprises:
depositing glass onto said topography, said depositing resulting in a planar surface of said glass, wherein said step of depositing glass comprises:
flowing a silicon oxide precursor over said topography,
and
hardening said precursor into a silicon oxide, and
lowering a dielectric constant of said glass, wherein said step of
lowering a dielectric constant of said glass comprises doping said silicon oxide with boron; and
providing a second level of said semiconductor device over said BSG.

70. (Original) The method in claim 69, wherein said step of providing a first level of a semiconductor device comprises providing a first level further comprising at least one conductive structure.

Claims 71-88 (Cancelled).